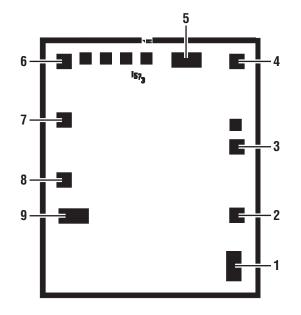


DICE/DWF SPECIFICATION

RH1573K Low Dropout PNP Regulator Driver



61mils × 72mils, 12mils thick. †Backside metal: Alloyed gold layer (K designator) Backside potential: lowest (GND) voltage

PAD FUNCTION

- 1. DRIVE
- 2. V_{IN}
- 3. V_{OUT}
- 4. COMP
- 5. GND1**
- 6. FB
- 7. LATCH
- 8. SHDN
- 9. GND2**

**GND1 and GND2 are connected together to form GND

DIE CROSS REFERENCE

| LTC Finished | Order |
|----------------------|---------------------------|
| Part Number | Part Number |
| RH1573K [†] | RH1573KDICE† |
| RH1573K [†] | RH1573KDWF* ^{,†} |

Please refer to LTC standard product data sheet for other applicable product information.

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DICE/DWF ELECTRICAL TEST LIMITS $T_A = 25$ °C.

| PARAMETER | CONDITIONS | MIN | MAX | UNITS |
|------------------------------------|---|-------|----------|----------|
| Reference Voltage | I _{DRIVE} = 20mA, T _J = 25°C | 1.252 | 1.278 | V |
| Line Regulation (V _{FB}) | I _{DRIVE} = 20mA, 3V < V _{IN} < 7V | | 2 | mV |
| Load Regulation (V _{FB}) | I _{DRIVE} = 20mA to 250mA | | 18 | mV |
| FB Pin Bias Current | V _{FB} = 1.265V | | 4 | μA |
| DRIVE Pin Current | $V_{FB} = 1.35V$, $V_{DRIVE} = 7V$ $V_{FB} = 1.15V$, $V_{DRIVE} = 1.5V$ | 290 | 1.2 | mA mA |
| DRIVE Pin Saturation Voltage | I _{DRIVE} = 20mA, V _{FB} = 1.15V I _{DRIVE} = 250mA, V _{FB} = 1.15V | | 0.2 1 | V |



^{*}DWF = DICE in wafer form.

DICE/DWF SPECIFICATION

RH1573K

DICE/DWF ELECTRICAL TEST LIMITS $T_A = 25$ °C.

| PARAMETER | CONDITIONS | MIN | MAX | UNITS |
|--|------------------------|------|------|-------|
| SHDN Pin Threshold Voltage | | 1 | 1.5 | V |
| SHDN Pin Current | V _{SHDN} = 5V | | 300 | μΑ |
| LATCH Pin Latch-Off Threshold Voltage | | 1.1 | 1.8 | V |
| LATCH Pin Charging Current | | 4 | 10 | μA |
| LATCH Pin Latching Current | | | 0.85 | mA |
| V _{IN} to V _{OUT} Differential Threshold for Latch Disable | | 0.55 | 0.8 | V |
| Input Quiescent Current | V _{IN} = 7V | | 2.8 | mA |
| Minimum Input Voltage for Bias Operation | | 2.4 | | V |

Note 1: For circuit operation and application information refer to LT1573 data sheet.

Note 2: For post radiation performance contact factory.

Wafer level testing is performed per the indicated specifications for dice. Considerable differences in performance can often be observed for dice versus packaged units due to the influences of packaging and assembly on certain devices and/or parameters. Please consult factory for more information on dice performance and lot qualifications via lot sampling test procedures.

Dice data sheet subject to change. Please consult factory for current revision in production.

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